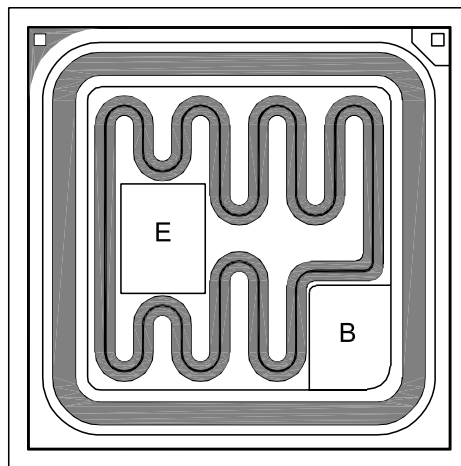


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	19 X 19 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 X 4.3 MILS
Emitter Bonding Pad Area	3.5 X 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

Geometry



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

30,475

PRINCIPAL DEVICE TYPES

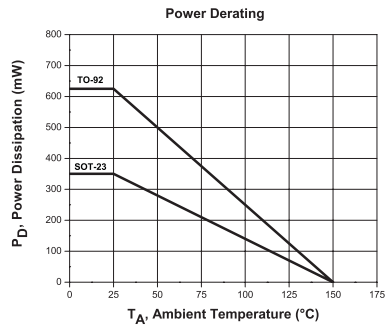
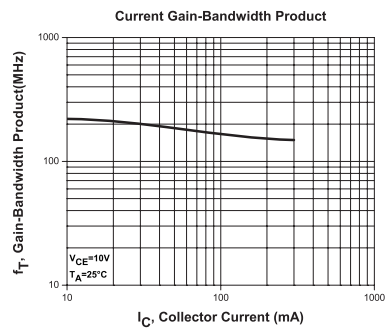
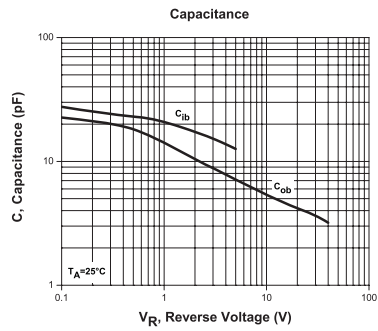
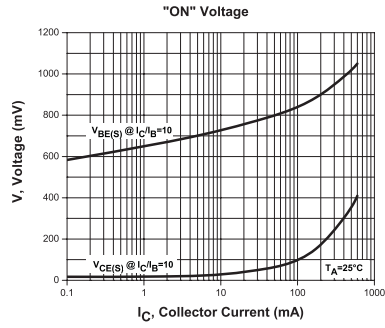
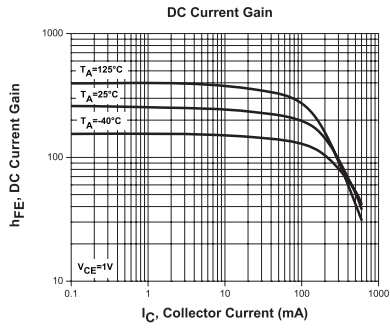
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R1 (28-August 2008)



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